

isc Silicon NPN Power Transistor

BUX98PI

DESCRIPTION

- High voltage high speed
- High Current Capability
- Fast Switching Speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

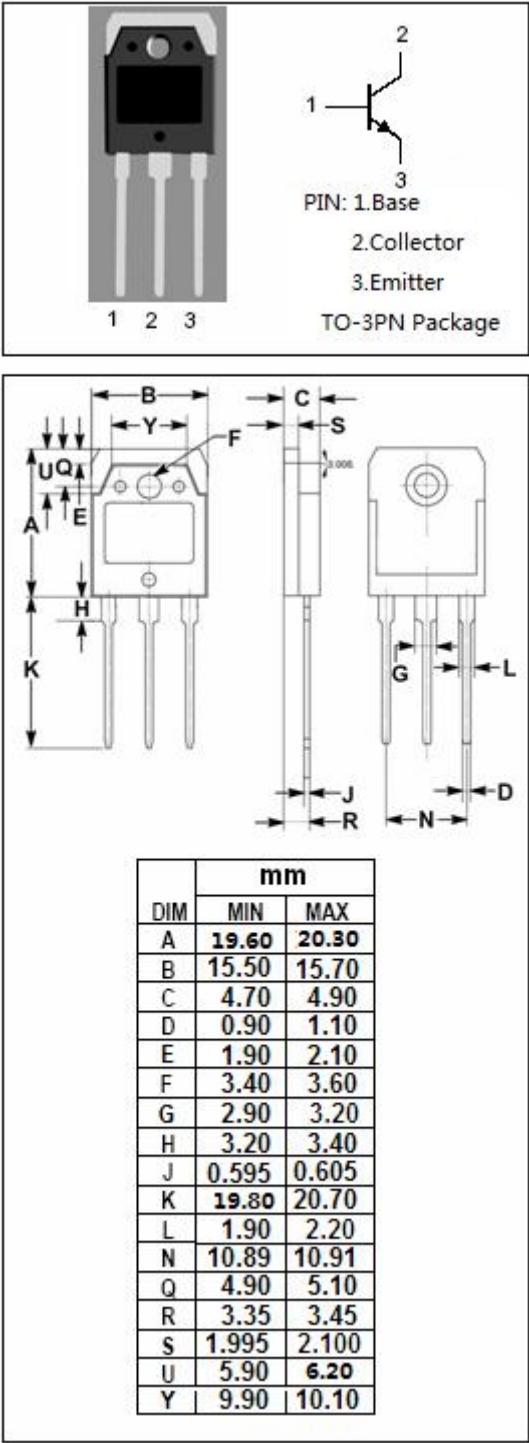
- High voltage high speed transistor suited for use on the 220V and 380V mains
- Suitable for switch mode power supplies,DC and AC motor motor control

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	850	V
V _{CEO}	Collector-Emitter Voltage	450	V
V _{EBO}	Emitter-Base Voltage	7	V
I _C	Collector Current-Continuous	30	A
I _{CM}	Collector Current-peak	45	A
I _B	Base Current-Continuous	6	A
I _{BM}	Base Current-peak	10	A
P _C	Collector Power Dissipation @T _C =25°C	200	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-65~150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	0.63	°C/W



isc Silicon NPN Power Transistor**BUX98PI****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)} *	Collector-Emitter Sustaining Voltage	I _C = 200mA ; L=25mH	450			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = 20A ; I _B = 4A			0.9	V
V _{BE(sat)} *	Base-Emitter Saturation Voltage	I _C = 20A ; I _B = 4A			1.5	V
I _{CER}	Collector Cutoff Current(R _{BE} =5Ω)	V _{CE} =V _{CEV} ; V _{CE} =V _{CEV} ; T _C =100°C			0.2 1	mA
I _{CEV}	Collector Cutoff Current	V _{CE} = V _{CEV} ; V _{BE} =-1.5V V _{CE} = V _{CEV} ; V _{BE} =-1.5V; T _C =100°C			0.2 1	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			1	mA

Switching Times

t _s	Storage Time	I _C = 20A ; I _{B1} =-I _{B2} = 4A; V _{CC} = 50V; V _{clamp} =450V V _{BB} =-5V; R _{BB} =0.62Ω L _C =0.12mH, T _j =100°C			4.5	μ s
t _f	Fall Time				0.4	μ s
t _c	Crossover Time				0.7	μ s

*Pulse: pulse duration=300us, duty cycle=1.5%